

SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBS00340

I_o = 30mA

V_R = 40 Volts



Features

Designed for mounting on small surface.

Extremely thin package.

Low stored charge.

Majority carrier conduction.

Mechanical data

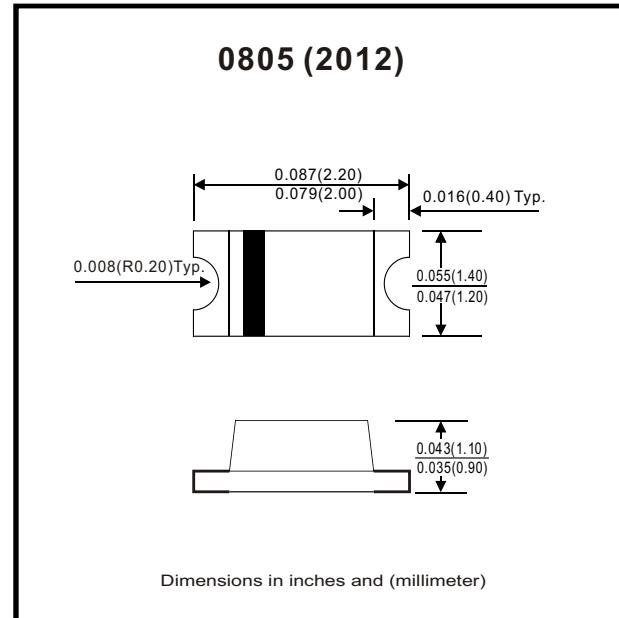
Case: 0805(2012) standard package,
molded plastic.

Terminals: Gold plated, solderable per
MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.0048 gram(approx.).



Dimensions in inches and (millimeter)

Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V _{RRM}			45	V
Reverse voltage		V _R			40	V
Average forward current		I _o			30	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	I _{FSM}		500		mA
Power Dissipation		P _D			200	mW
Sunction temperature		T _{TG}	-40		+125	°C
Junction temperature		T _j			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 1 mA DC	V _F			0.37	V
Reverse current	V _R = 30V V _R = 40V	I _R			0.50 1.00	uA
Capacitance between terminals	F = 1 MHZ and 1 VDC reverse voltage	C _T		2		pF

RATING AND CHARACTERISTIC CURVES (CDBS00340)

Fig. 1 - Forward characteristics

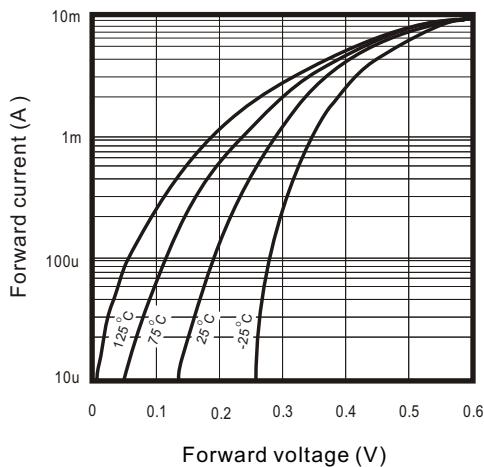


Fig. 2 - Reverse characteristics

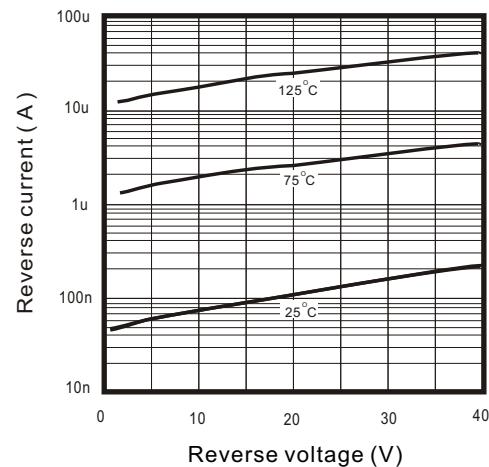


Fig.3 - Capacitance between terminals characteristics

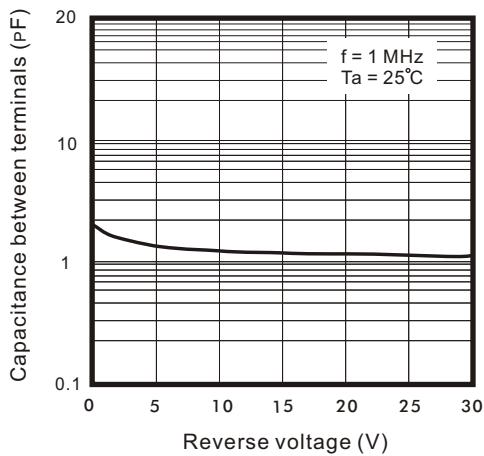


Fig.4 - Derating curve

